

1SS286

SCHOTTKY BARRIER DIODE

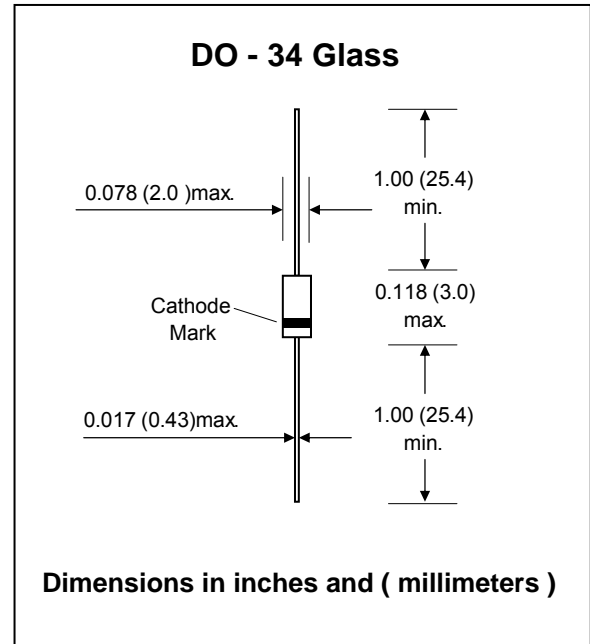
FEATURES :

- Very Low I_R
- Low V_F and high efficiency.
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-34 Glass Case

Weight: approx. 0.11g



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified)

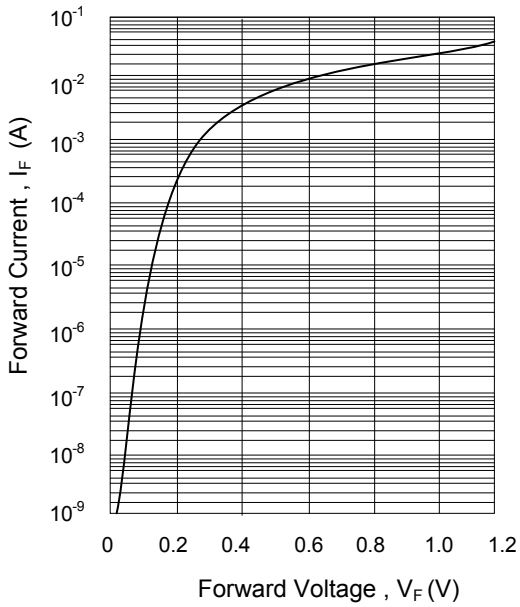
Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	25	V
Average Rectified Current	I _o	35	mA
Power Dissipation	P _D	150	mW
Junction Temperature	T _J	100	°C
Storage temperature range	T _{stg}	-55 to + 100	°C

Electrical Characteristics (T_J = 25°C unless otherwise noted)

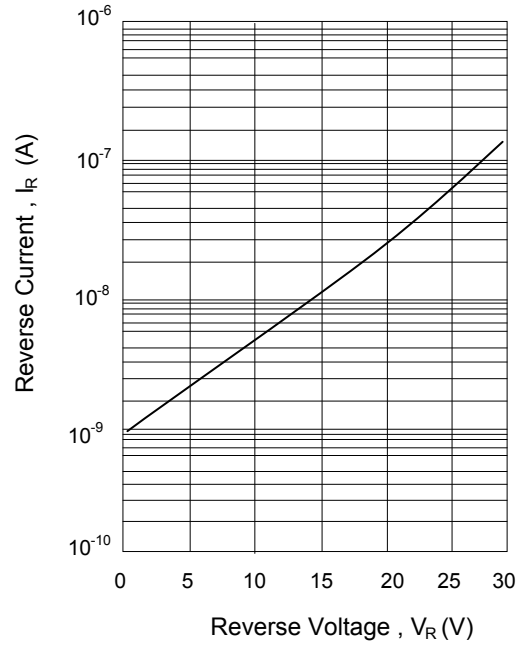
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	I _R	V _R = 10 V	-	-	10	nA
Reverse Voltage	V _R	I _R = 10 μA	25	-	-	V
Forward Voltage	V _F	I _F = 10 mA	-	-	0.6	V
Forward Current	I _F	V _F = 1 V	3.0	-	-	mA
Diode Capacitance	C _d	V _R = 0V, f = 1MHz	-	-	1.2	pF
Diode Capacitance Deviation	ΔC _d	V _R = 0V, f = 1MHz	-	-	±0.05	pF
Forward Voltage Deviation	ΔV _F	I _F = 10 mA	-	-	±5	mV

RATING AND CHARACTERISTIC CURVES (1SS286)

Forward Current VS. Forward Voltage



Reverse Current VS. Reverse Voltage



Diode capacitance VS. Reverse Voltage

